

Supporting Information

Figure S1. Wide-angle X-ray diffraction spectra of FS111 as-cast and after annealing at 140 °C for 5 min.

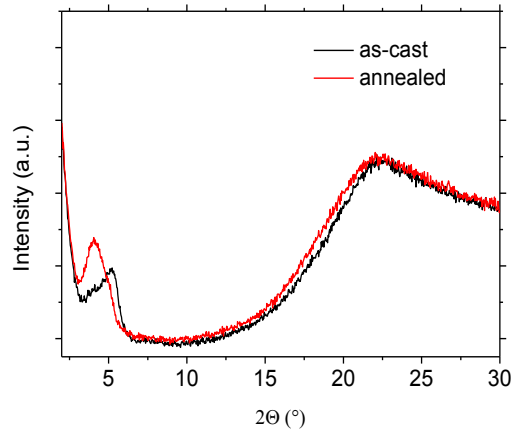


Figure S2. Transfer curve of a PVP-based OFET device using FS111 operating at –25 V with root square of I_D for parameter extraction (a) and gate leakage current for calculation of I_D/I_G -ratio (b).

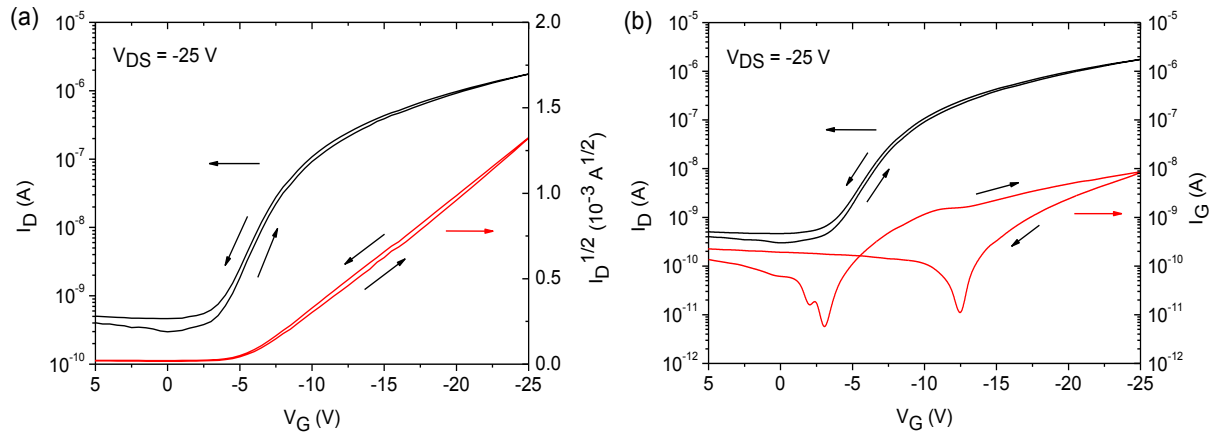


Table S1. Extracted parameters for FS111 using PVP dielectrics on glass at supply voltages of –25 V.

Characteristic	FS111 on PVP/glass at supply voltages of –25 V
Field-effect mobility μ_{sat}	0.1 cm ² /Vs
Threshold voltage V_T	–5 V
On/Off-current ratio	5×10^3
Subthreshold Swing	2.6 V/dec

Figure S3. Transfer characteristics of (a) spin-coated FS111 on SU-8; (b) spin-coated FS111 on PVP and (c) automatically μ -dispensed FS111 on SU-8 demonstrating the relation of the drain current I_D to the gate current I_G .

